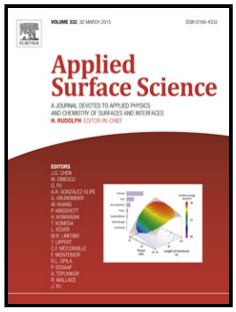

Title: Influence of growth and annealing temperature on the strain and surface morphology of $Ge_{995}Sn_{0.005}$ epilayer

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- $Ge_{0.995}Sn_{0.005}$ alloys were grown on Si (100) by MBE at 220~500 ºC.
- Surface roughening was enhanced with the increase of growth temperature.
- Non-monotonic temperature dependence of the surface roughening was observed.
- The incorporation of Sn into Ge helped release the residual heteroepitaxial strain.
- The influence of annealing temperature on $Ge_{0.995}Sn_{0.005}$ was also investigated.